

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

Sheet 1 of 1

ATTY. DOCKET NO.

SERIAL NO.

M-300 US

06/843,454

APPLICANT

Richard A. Blanchard

FILING DATE

03/24/86

GROUP

114

LIST OF RELEVANT ART CITED BY APPLICANT

(Indicate on several sheets if necessary)

U.S. PATENT DOCUMENTS

CLASS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AA	3398339	8/16/83	Blanchard et al.	29	571	9/9/81
AB	4639754	1/27/87	Wheatley, Jr. et al.	357	23.4	2/25/85
AC	4682405	7/28/87	Blanchard et al.	29	571	7/22/85
AD						
AE						
AF						
AG						
AH						
AI						
AJ						
AK						

FOREIGN PATENT DOCUMENTS

CLASS	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION
AL	53149771	12/27/78	Japan (Matsushita Elec.)	357	23.4	X
AM	55146976	11/15/80	Japan (Hideshima)			X
AN						
AO						
AP						

OTHER

ART (Including Author, Title, Date, Pertinent Pages, Etc.)

AR	Baliga et al. "THE INSULATED GATE TRANSISTOR: A NEW THREE-TERMINAL MOS-CONTROLLED BIPOLAR POWER DEVICE", IEEE Transactions on Electron Devices, Vol. ED-31, No. 6, June 1984, pgs. 821-828.
AS	Ueda et al. "A NEW VERTICAL POWER MOSFET STRUCTURE WITH EXTREMELY REDUCED ON-RESISTANCE", IEEE Transactions on Electron Devices, Vol. ED-32, No. 1, January 1985, pgs. 2-6
AT	Rung et al. "DEEP TRENCH ISOLATED CMOS DEVICES", IEDM 1982, pgs. 237-240.

EXAMINER

D. T. Ozaki

DATE CONSIDERED

12-11-87

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.